

<b>SANYO</b>	No.1047B	<b>2SA1246/2SC3114</b>
		PNP/NPN Epitaxial Planar Silicon Transistors
<b>High-<math>V_{EBO}</math>, AF Amp Applications</b>		

**Features**

- High  $V_{EBO}$
- Wide ASO and highly resistant to breakdown.

( ) : 2SA1246

**Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$**

			unit
Collector to base voltage	$V_{CBO}$	(-)60	V
Collector to emitter voltage	$V_{CEO}$	(-)50	V
Emitter to base voltage	$V_{EBO}$	(-)15	V
Collector current	$I_C$	(-)150	mA
Collector Current(Pulse)	$I_{CP}$	(-)300	mA
Collector dissipation	$P_C$	400	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

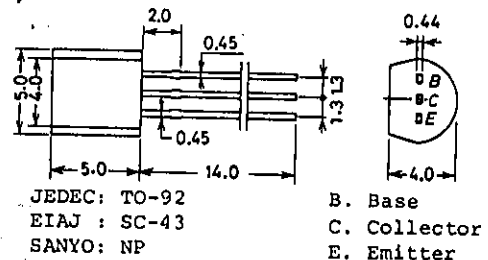
**Electrical Characteristics/ $T_a = 25^\circ\text{C}$**

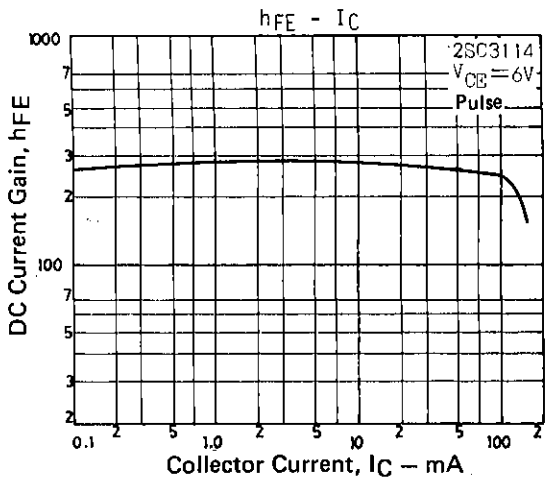
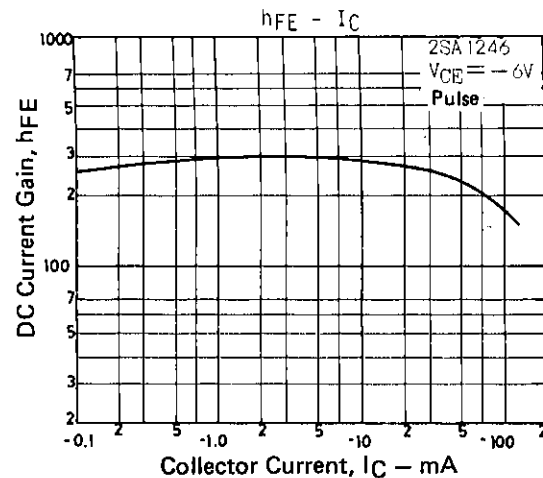
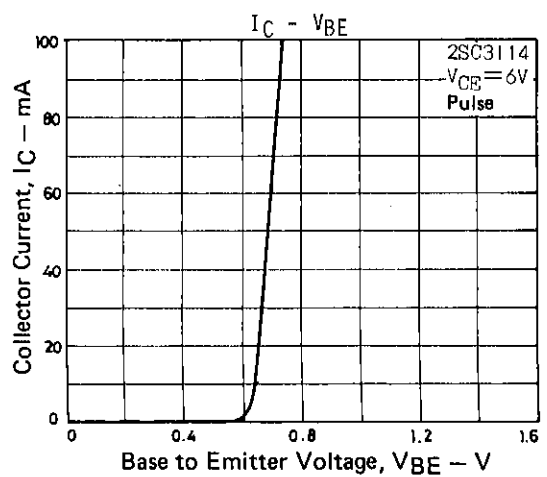
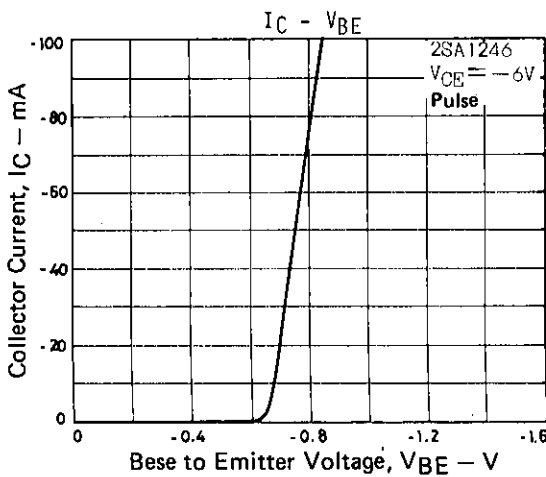
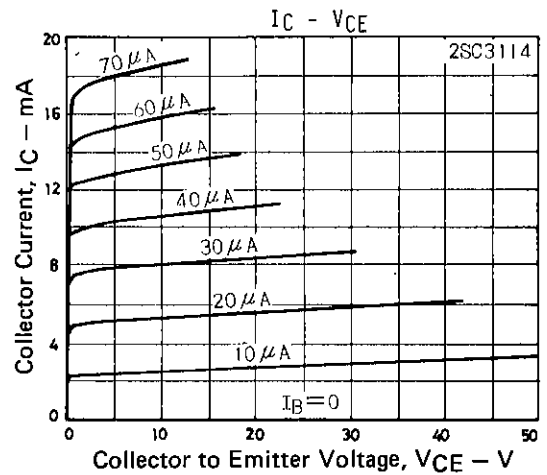
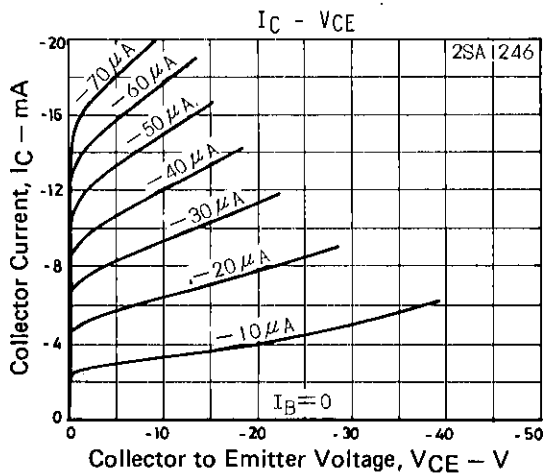
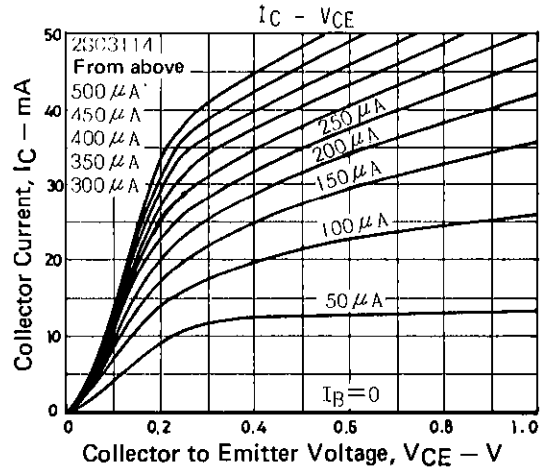
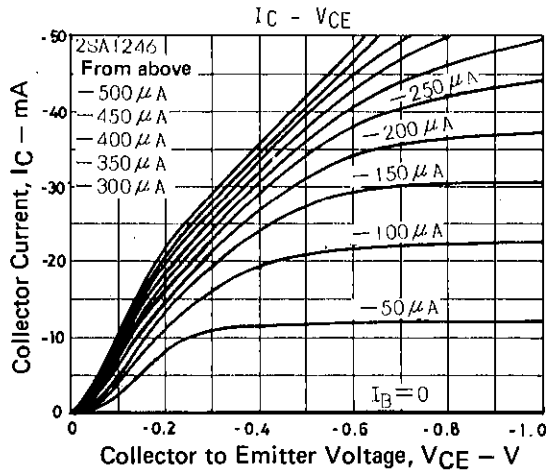
			min	typ	max	unit
Collector cutoff current	$I_{CBO}$	$V_{CB}=(-)40\text{ V}, I_E=0$			(-)0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB}=(-)10\text{ V}, I_C=0$			(-)0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=(-)6\text{ V}, I_C=(-)1\text{ mA}$	100*		560*	
Gain-bandwidth product	$f_T$	$V_{CE}=(-)6\text{ V}, I_C=(-)1\text{ mA}$		100		MHz
Common base output capacitance	$C_{ob}$	$V_{CB}=(-)6\text{ V}, f=1\text{ MHz}$		3.0		pF
C-E saturation voltage	$V_{CE(sat)}$	$I_C=(-)50\text{ mA}, I_B=(-)15\text{ mA}$		(4.2)	(-)0.5	V
C-B breakdown voltage	$V_{(BR)CBO}$	$I_C=(-)10\text{ }\mu\text{A}, I_E=0$	(-)60			V
C-E breakdown voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{ mA}, R_{BE}=\infty$	(-)50			V
E-B breakdown voltage	$V_{(BR)EBO}$	$I_E=(-)10\text{ }\mu\text{A}, I_C=0$	(-)15			V

\* The 2SA1246/2SC3114 are classified as follows according to  $h_{FE}$  at 1 mA.

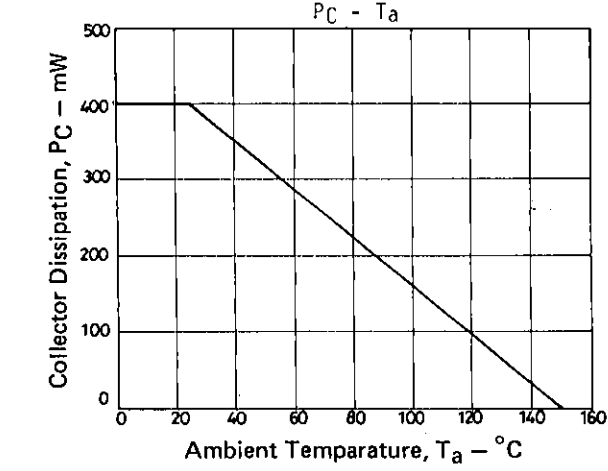
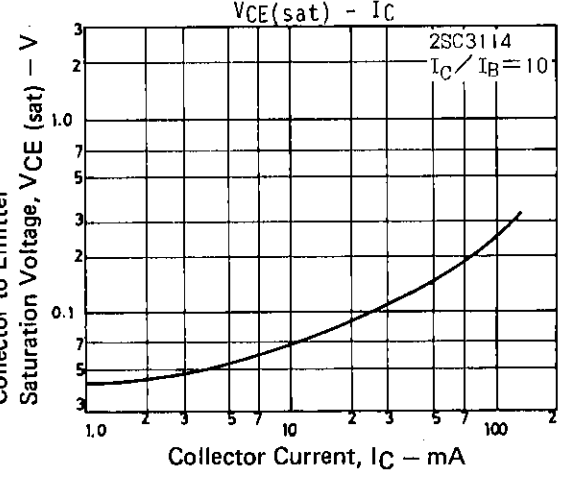
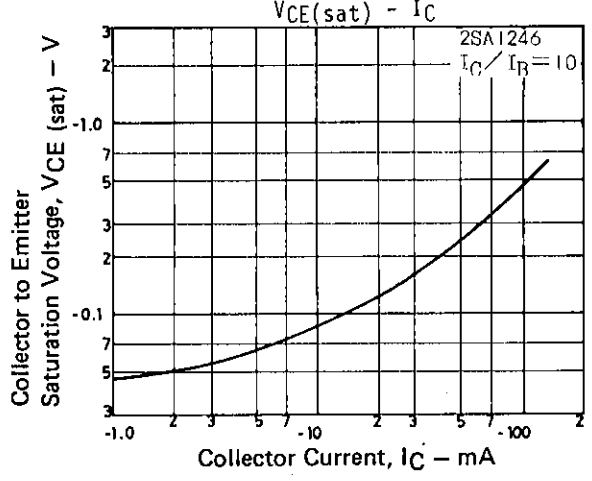
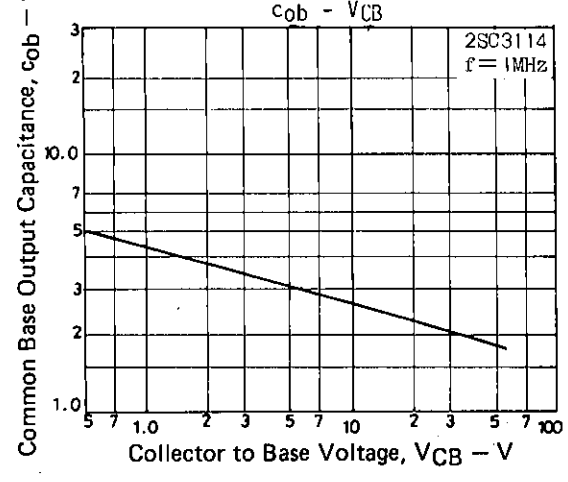
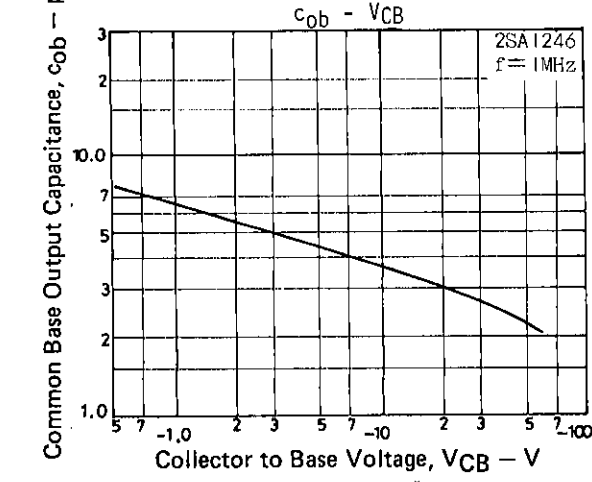
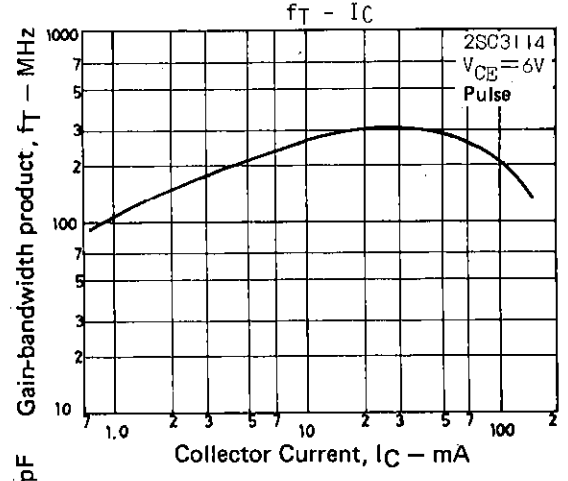
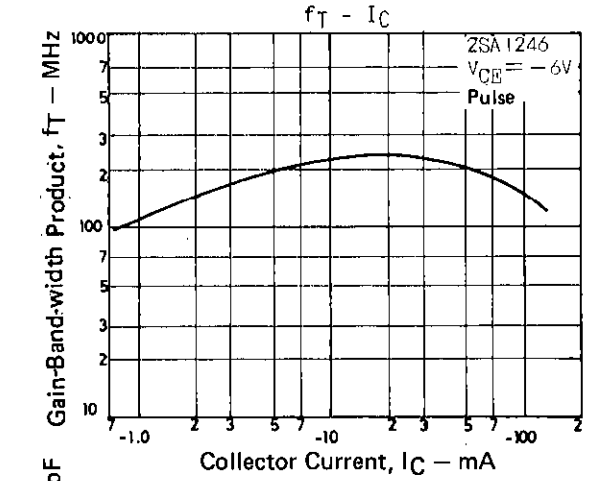
100 R	200	140 S	280	200 T	400	280 U	560
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**Package Dimensions 2003A**  
(unit: mm)





2SA1246/2SC3114



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